## MN74HC02/MN74HC02S

#### Quad 2-Input NOR Gates

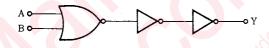
#### ■ Outline

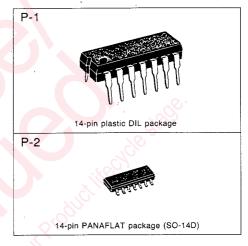
The MN74HC02/MN74HC02C is a 2-input positive logic NOR gate having four built-in circuits in one chip.

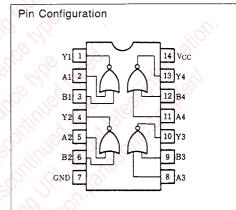
Owing to the silicon gate CMOS process, this NOR gate has realized low power consumption and high noise immunity equivalent to those of a standard CMOS and the operation speed as high as of an LS TTL. The buffer added to the gate output improves the input/output transfer characteristic and minimizes the propagation delay time fluctuation caused by the load capacity increase. The MN74HC02/ MN74HC02S can directly drive ten LS TTL inputs.

To protect the input and output against electrostatic breakdown, a resistor and a diode are used for the  $V_{\text{CC}}$  and the GND. The pin configuration and the function are the same as those of the standard 54LS/74LS logic family.

#### ■ Logic Diagram (1 Gate)







■ Absolute Maximum Ratings

Item			Symbol	Rating	Unit
Supply voltage			V <sub>cc</sub>	-0.5~+7.0	V
Input output voltage			V <sub>I</sub> , V <sub>O</sub>	-0.5~V <sub>cc</sub> +0.5	V
Input protective diode current			$I_{IK}$	<u>±20</u>	mA
Output parasitic diode current			I <sub>ok</sub>	±20	mA
Output current			Io	±25	mA
Supply current			I <sub>CC</sub> , I <sub>GND</sub>	±50	mA
Storage temperature			$T_{stg}$	−65~+150	°C
Power dissipation	MN74HC02	$Ta = -40 \sim +60^{\circ}C$	ъ	400	mW
		$Ta = +60 \sim +85^{\circ}C$	$P_D$	Decrease to 200mW at the rate of 8mW/°C	¬ mw
	MN74HC02S	Ta=-40~+60°C	D	275	mW
	WIN /4HCU2S	$Ta = +60 \sim +85^{\circ}C$	$\mathbf{P}_{D_{j}}$	Decrease to 200mW at the rate of 3.8mW/°C	7 mvv

### ■ Recommended Operating Conditions

Item	Symbol	V <sub>cc</sub> (V)	Rating	Unit	
Operating power supply voltage	Vcc		1.4~6.0	V	
Input output voltage	V <sub>I</sub> , V <sub>O</sub>		0~V <sub>cc</sub>	V	
Operating temperature	T <sub>A</sub>		-40~+85	°C	
		2.0	0~1000	ns	
Input rise, fall time	t <sub>r</sub> , t <sub>f</sub>	4.5	0~500	ns	
		6.0	0~400	ns	

#### ■ DC Characteristics (GND=0V)

	Symbol	V <sub>cc</sub> (V)	Test Condition			Temperature					
Item			Vı	Ţ		Ta=25°C			Ta=-40~+85°C		Unit
				Io	Unit	min.	typ.	max.	min.	max.	`
		2.0			•	1.5			1.5		
Input voltage high level	$V_{IH}$	4.5				3.15			3.15		V
		6.0				4.2			4.2		
		2.0						0.3		0.3	
Input voltage low level	$V_{IL}$	4.5						0.9		0.9	V
		6.0					<b>X</b>	1.2		1.2	
		2.0		-20.0	μΑ	1.9	2.0		1.9		
		4.5		-20.0	$\mu A$	4.4	4.5		4.4		
Output voltage high level	$V_{OH}$	6.0	$V_{IL}$	-20.0	$\mu$ A	5.9	6.0		5.9		V
		4.5		-4.0	mA	3.92	0		3.84		
		6.0		-5.2	mA	5.48	7/5		5.34		
		2.0		20.0	$\mu$ A	G.	0.0	0.1		0.1	)
		4.5	$V_{IH}$	20.0 🕻	$\mu$ A		0.0	0.1		0.1	
Output voltage low level	Vol	6.0	or	20.0	$\mu$ A	Po. K.	0.0	0.1	•.4	0.1	V
		4.5	$V_{IL}$	4.0	mA		00	0.26	(%)	0.33	
		6.0	6	5.2	mA		1110	0.26	XO2	0.33	
Input leakage current	Iı	6.0	$V_i = V_{CC}$	or GNI	) <u>*</u> @\		1	±0.1	0.0	±1.0	μΑ
Static supply current	$I_{cc}$	6.0	$V_I = V_{CC}$	or GNE	$I_0 = 0$	<sup>-</sup> C <sub>O</sub> ,	16	2.0		20.0	μΑ

## ■ AC Characteristics (GND=0V, Input transition time≤6ns, C<sub>L</sub>=50pF)

	Symbol	V <sub>cc</sub> (V)	Test Condition	~G).					
Item				Ta=25°C			Ta=-40~+85°C		Unit
				min.	typ.	max.	min.	max.	] .
		2.0		0,12	25	75		95	
Output rise time	t <sub>TLH</sub>	4.5	<i>K</i> C		8	15		19	ns
		6.0		"Un	7	13		16	
13/1		2.0	113.11	$D_{a}$	20	75		95	
Output fall time	trHL	4.5	@ '.j.!		7	15		19	ns
		6.0	Sys Hilly		6	13		16	
		2.0			25	75		95	
Propagation time (L→H)	t <sub>PLH</sub>	4.5			8	15		19 '	ns
		6.0			7	13		16	
		2.0			25	75		95	
Propagation time (H→L)	t <sub>PHL</sub>	4.5			8	15		19	ns
		6.0			7	13		16	

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